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Photoluminescence Study of Nitrogen-Related States in ZnSe

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Abstract

Photoluminescence of N-doped ZnSe crystals is studied at temperatures between 10 and 300 K. Doping with N leads to the formation of simple Nbased donor and acceptor defects, as well as associative N-based acceptors. The nature and the structure of N-based luminescence centres and the mechanisms of radiative recombination are discussed.